2SC460, 2SC461

Silicon NPN Epitaxial Planar

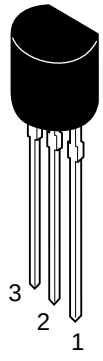
HITACHI

Application

- 2SC460 high frequency amplifier, mixer
- 2SC461 VHF amplifier, mixer

Outline

TO-92 (2)



1. Emitter
2. Collector
3. Base

Hitachi semiconductor

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	2SC460	2SC461	Unit
Collector to base voltage	V_{CBO}	30	30	V
Collector to emitter voltage	V_{CEO}	30	30	V
Emitter to base voltage	V_{EBO}	5	5	V
Collector current	I_C	100	100	mA
Collector power dissipation	P_C	200	200	mW
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	–55 to +150	–55 to +150	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	2SC460			2SC461			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	—	—	30	—	—	V	I_C = 10 µA, I_E = 0
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	30	—	—	30	—	—	V	I_C = 1 mA, R_{BE} = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	5	—	—	V	I_E = 10 µA, I_C = 0
Collector cutoff current	I_{CBO}	—	—	0.5	—	—	0.5	µA	V_{CB} = 18 V, I_E = 0
Emitter cutoff current	I_{EBO}	—	—	0.5	—	—	0.5	µA	V_{EB} = 2 V, I_C = 0
Base to emitter voltage	V_{BE}	—	0.63	0.75	—	0.63	0.75	V	V_{CE} = 12 V, I_C = 2 mA
DC current transfer ratio	h_{FE}*[1]	35	—	200	35	—	200		V_{CE} = 12 V, I_C = 2 mA
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	0.6	1.1	—	0.6	1.1	V	I_C = 10 mA, I_B = 1 mA
Gain bandwidth product	f_T	—	230	—	—	230	—	MHz	V_{CE} = 12 V, I_C = 2 mA
Collector output capacitance	C_{ob}	—	1.8	3.5	—	1.8	3.5	pF	V_{CB} = 10 V, I_E = 0, f = 1 MHz
10.7 MHz power gain	PG	26	29	—	—	—	—	dB	V_{CE} = 6 V, I_E = –1 mA f = 10.7 MHz
100 MHz power gain	PG	—	—	—	13	17	—	dB	V_{CE} = 6 V, I_E = –1 mA f = 100 MHz
Noise figure	NF	—	2.0	—	—	—	—	dB	V_{CE} = 6 V, I_E = –1 mA f = 1MHz R_g = 500Ω

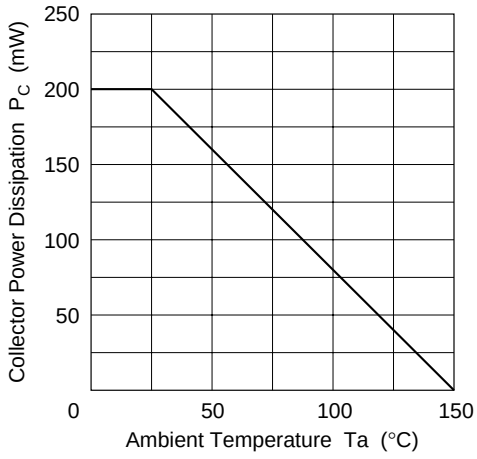
Note: 1. The 2SC460 and 2SC461 are grouped by h_{FE} as follows.

A	B	C
35 to 70	60 to 120	100 to 200

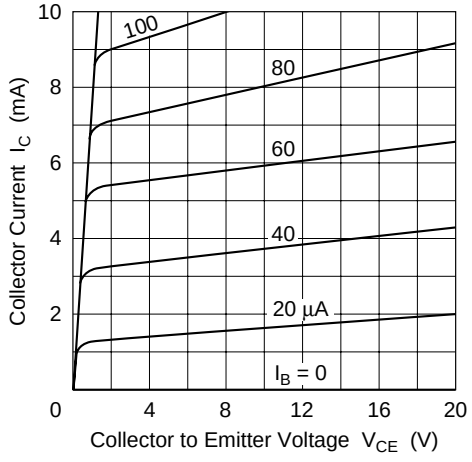
Small Signal y Parameters (V_{CE} = 6 V, I_C = 1 mA, Emitter Common)

Item	Symbol	f	2SC460A, 2S461A	2SC460B, 2SC461B	2SC460C, 2SC461C	Unit
Input admittance	yie	455 kHz	0.58 + j0.074	0.42 + j0.068	0.30 + j0.051	mS
		4.5 MHz	0.65 + j0.79	0.50 + j0.7	0.35 + j0.57	
		10.7 MHz	0.91 + j2.0	0.61 + j1.9	0.39 + j1.3	
		100 MHz	7.4 + j14	5.6 + j12	3.8 + j6.0	
Reverse transfer admittance	yre	455 kHz	–j0.003	–j0.003	–j0.003	mS
		4.5 MHz	–j0.04	–j0.04	–j0.04	
		10.7 MHz	–j0.13	–j0.13	–j0.13	
		100 MHz	–j1.0	–j1.0	–j1.0	
Forward transfer admittance	yfe	455 kHz	38 – j0.1	37 – j0.1	37 – j0.2	mS
		4.5 MHz	35 – j1.0	35 – j1.2	34 – j1.8	
		10.7 MHz	34 – j2.5	34 – j2.5	33 – j4.5	
		100 MHz	28 – j20	28 – j19	20 – j19	
Output admittance	yoe	455 kHz	0.0098 + j0.009	0.013 + j0.009	0.016 + j0.012	mS
		4.5 MHz	0.02 + j0.09	0.023 + j0.092	0.03 + j0.10	
		10.7 MHz	0.11 + j0.4	0.11 + j0.4	0.12 + j0.4	
		100 MHz	0.40 + j1.7	0.50 + j2.0	0.83 + j2.0	

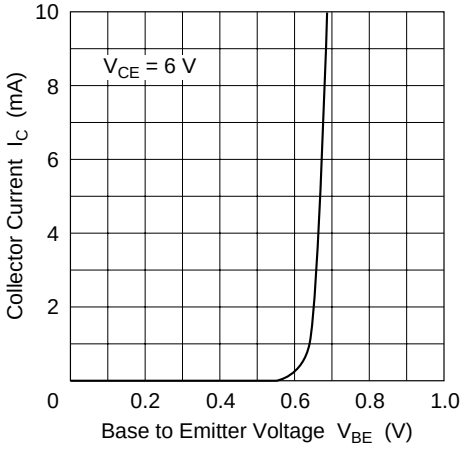
Maximum Collector Dissipation Curve



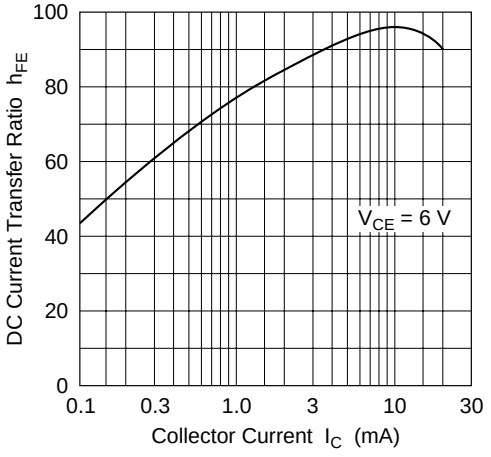
Typical Output Characteristics



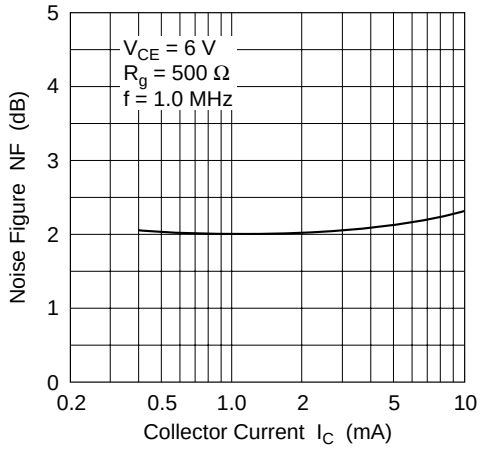
Typical Transfer Characteristics



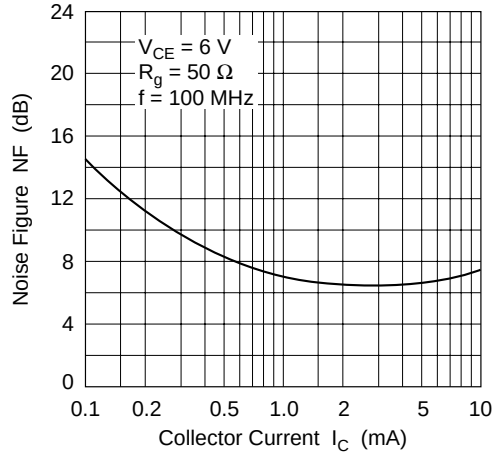
DC Current Transfer Ratio vs. Collector Current



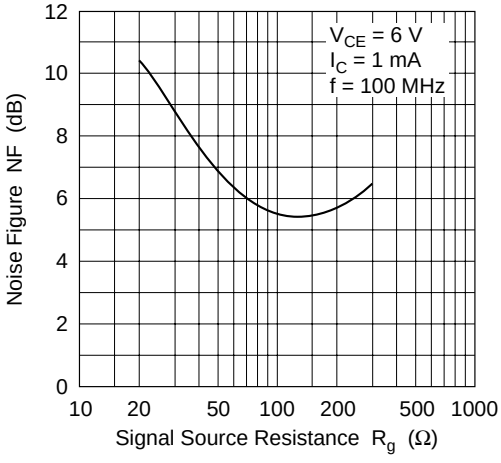
Noise Figure vs. Collector Current



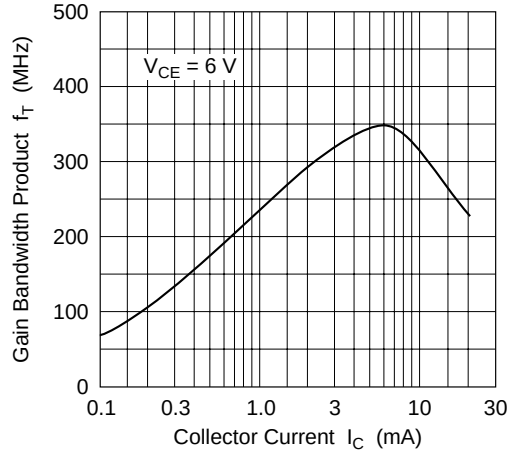
Noise Figure vs. Collector Current



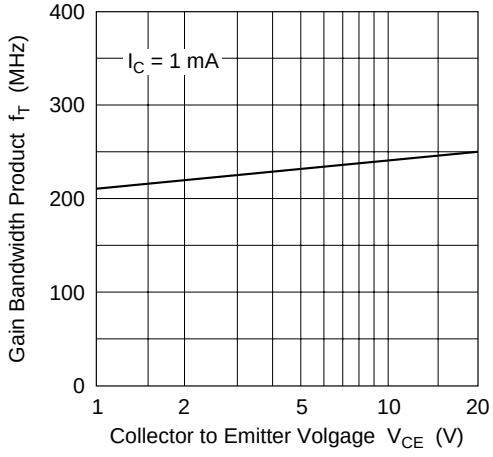
Noise Figure vs. Signal Source Resistance



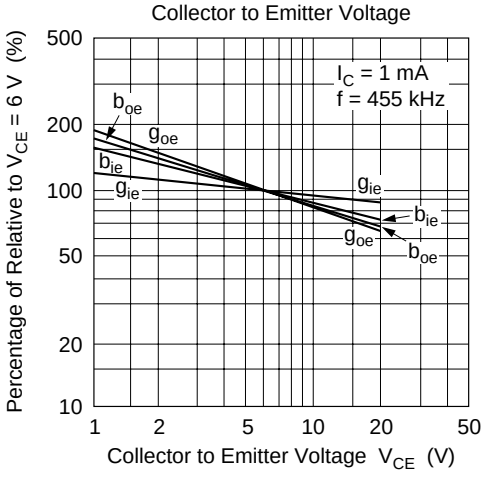
Gain Bandwidth Product vs. Collector Current



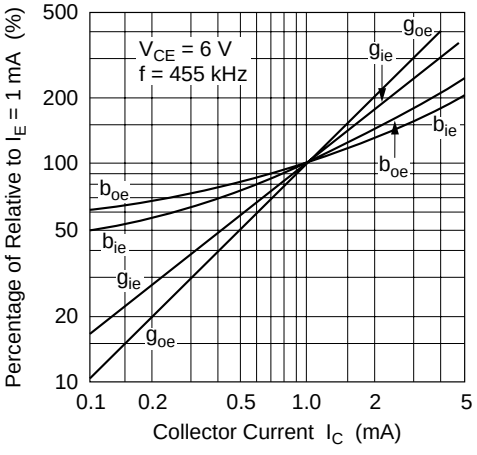
Gain Bandwidth Product vs.
Collector to Emitter Voltage



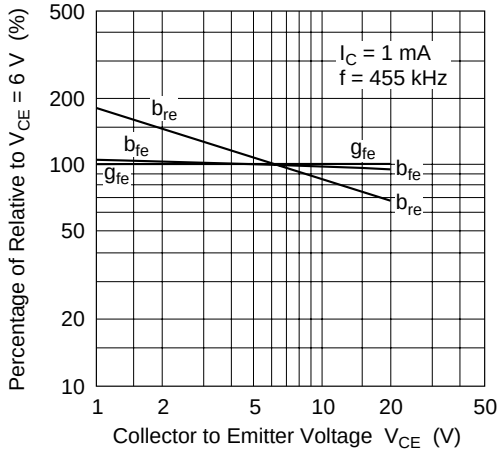
Input/Output Admittance vs.
Collector to Emitter Voltage



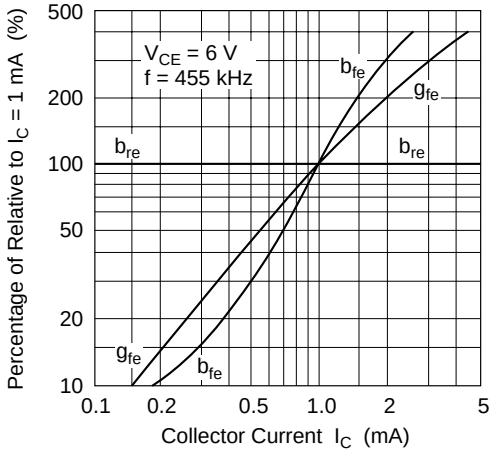
Input/Output Admittance vs.
Collector Current



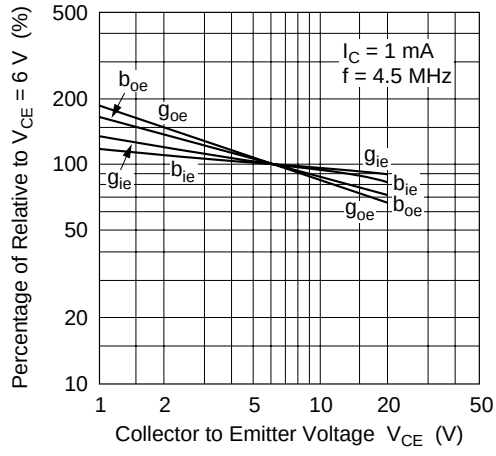
Transfer Admittance vs.
Collector to Emitter Voltage



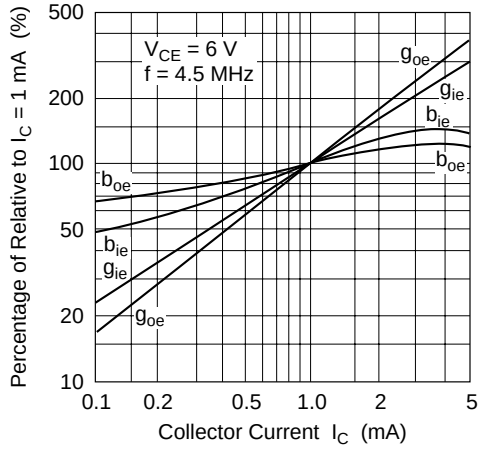
Transfer Admittance vs. Collector Current



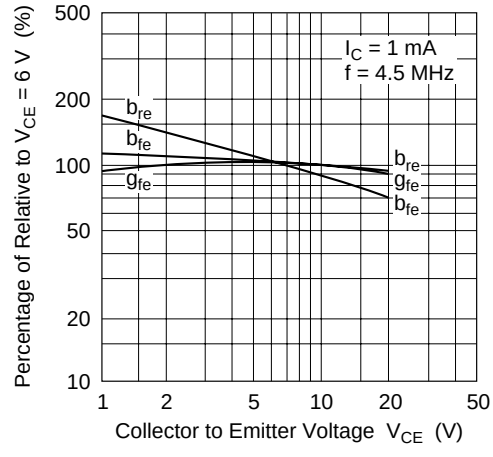
Input/Output Admittance vs. Collector to Emitter Voltage



Input/Output Admittance vs. Collector Current



Transfer Admittance vs. Collector to Emitter Voltage



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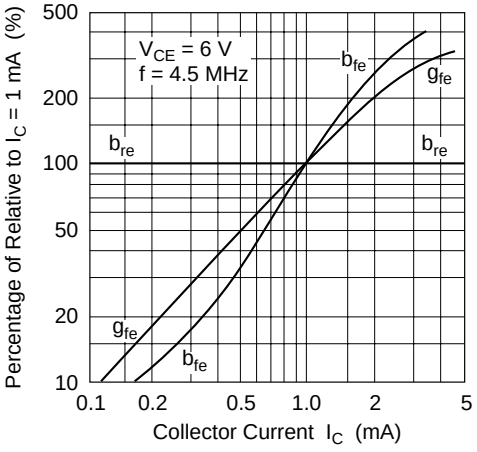
Collector Current



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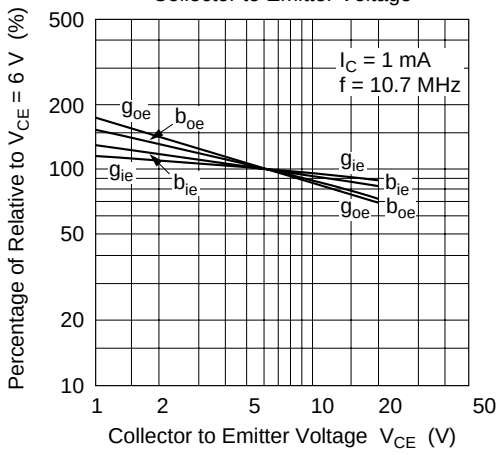

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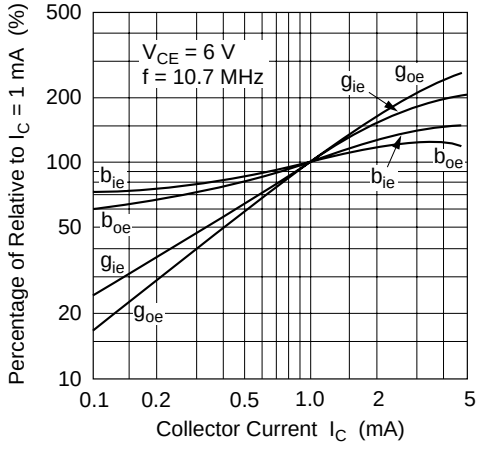

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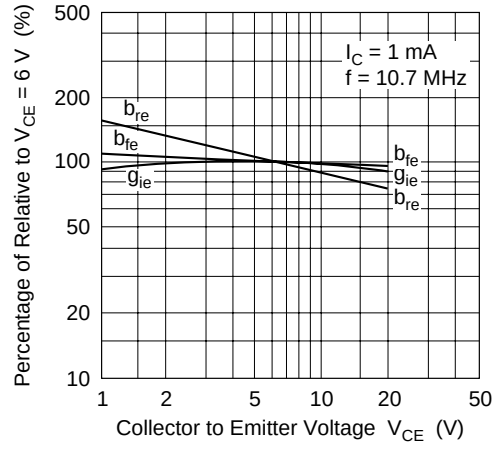

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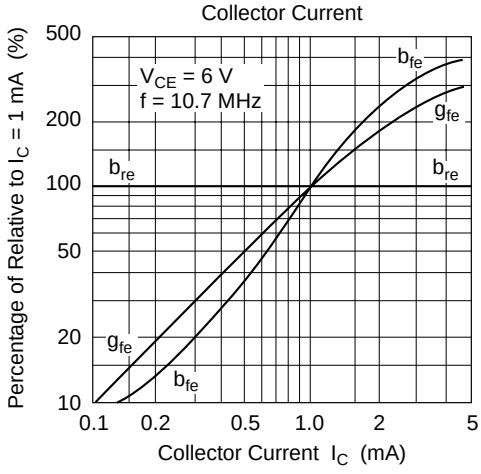

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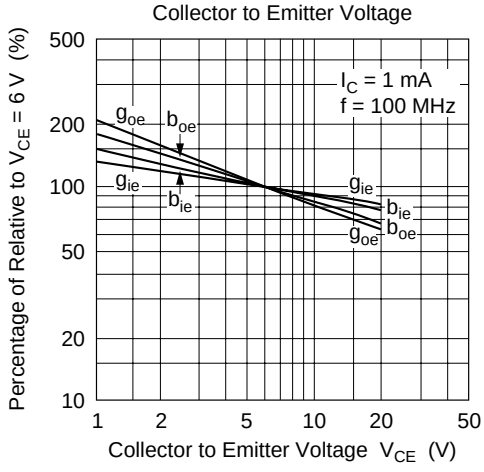

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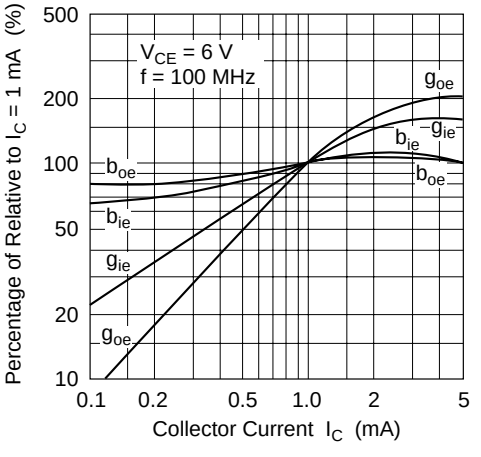

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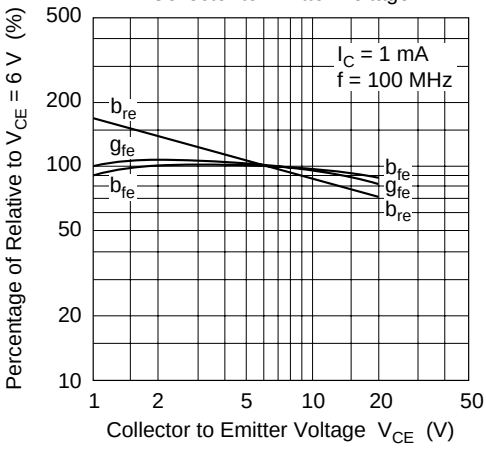

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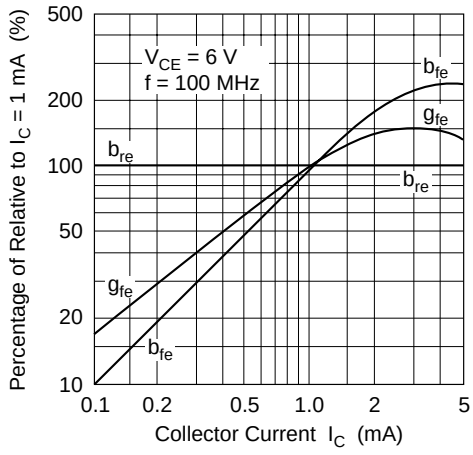
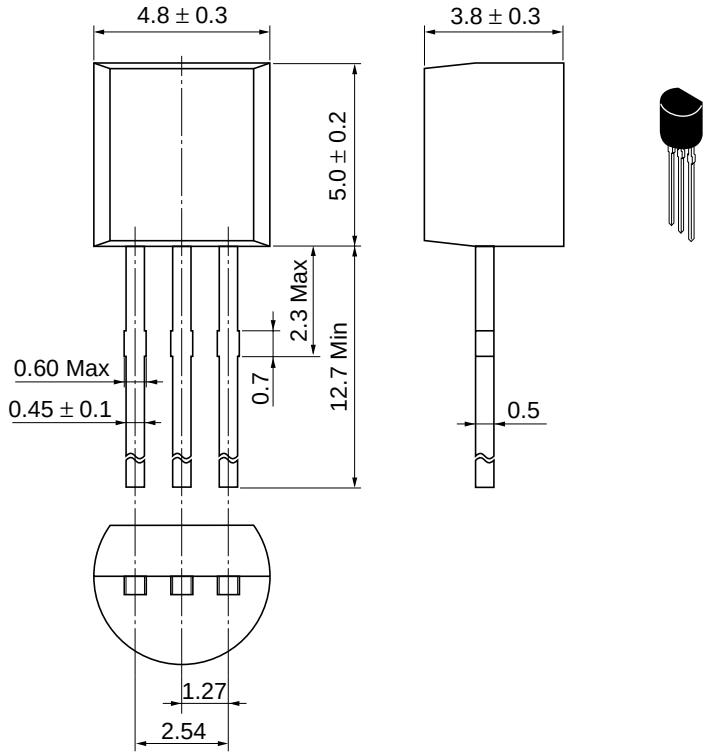


Unit: mm



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JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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HITACHI

Hitachi, Ltd.
Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose,CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building. No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX